	CMLDM8120 CMLDM8120G*	Cen	tra	тм			
		Semicon	ductor Cor		v.centralsemi.com		
SURF/	ACE MOUNT SILICON P-CHANNEL	DESCRIPTION:					
ENH	IANCEMENT-MODE			місоврис	CTOR devices		
	MOSFET	are enhancement-mode P-Channel MOSFETs,					
					IOS Process,		
					plifier and driver		
			applications. This MOSFET offers low r _{DS(on)} and low theshold voltage.				
	Centre		•				
		MARKING CODES: CMLDM8120: C81					
			20G*: C8G				
	SOT-563 CASE						
* Device is <i>Halog</i>	yen Free by design	FEATURE	ç.				
APPLICATIONS:		• Low rDS(on)					
Load/Power Switches		Low Threshold Voltage					
Power Supply Converter Circuits		Logic Level Compatible					
Battery Powe	red Portable Equipment	 Small SOT 	-563 package	1			
MAXIMUM RATINGS: (T _A =25°C)		SYMBOL			UNITS		
Drain-Source Voltage		V _{DS}		20	V		
Gate-Source Ve	0	V _{GS}		.0	V		
Continuous Drain Current (Steady State)		I _D		60 50	mA mA		
Continuous Drain Current, t≤5.0s Continuous Source Current (Body Diode)		I _D IS	950 360		mA		
Maximum Pulsed Drain Current, tp=10µs		I _{DM}	4.0		A		
Maximum Pulsed Source Current, tp=10µs		I _{SM}	4.0		А		
Power Dissipat	ion (Note 1)	PD	350		mW		
Power Dissipat	ion (Note 2)	PD	300		mW		
Power Dissipation (Note 3)		PD	150		mW		
	Storage Junction Temperature	T _J , T _{stg}		o +150 	°C		
Thermal Resist	ance	Θ_{JA}	3	57	°C/W		
	CHARACTERISTICS: (T _A =25°C						
SYMBOL		MIN	TYP 1.0	MAX 50	UNITS nA		
IGSSF, IGSSR	V _{GS} =8.0V, V _{DS} =0 V _{DS} =20V, V _{GS} =0		5.0	500 500	nA		
BV _{DSS}	V _{GS} =0, I _D =250µA	20	24	000	V		
V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.45	0.76	1.0	V		

 $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ 0.45 0.76 1.0 VGS(th) v_{SD} V_{GS}=0V, I_S=360mA 0.9 V V_{GS}=4.5V, I_D=0.95A Ω 0.085 0.15 rDS(ON) V_{GS}=4.5V, I_D=0.77A 0.085 0.142 Ω rDS(ON) V_{GS}=2.5V, I_D=0.67A 0.13 0.20 Ω rDS(ON) V_{GS}=1.8V, I_D=0.2A 0.19 0.24 Ω rDS(ON) V_{DS}=10V, I_D=0.81A 2.0 S 9FS V_{DS} =16V, V_{GS} =0, f=1.0MHz 80 pF C_{rss} C_{iss} V_{DS} =16V, V_{GS} =0, f=1.0MHz 200 pF V_{DS}=16V, V_{GS}=0, f=1.0MHz pF $\mathbf{C}_{\mathrm{OSS}}$ 60

 Notes:
 (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²

 (2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
 (3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

R6 (8-June 2015)

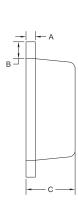


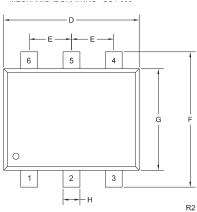
CMLDM8120 CMLDM8120G*

SURFACE MOUNT SILICON P-CHANNEL ENHANCEMENT-MODE MOSFET

ELECTRICA	L CHARACTERISTICS - Continued: (T _A =25°C u	nless otherwise noted)	
SYMBOL	TEST CONDITIONS	TYP	UNITS
Q _{g(tot)}	V _{DS} =10V, V _{GS} =4.5V, I _D =1.0A	3.56	nC
Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =1.0A	0.36	nC
Q _{gd}	V _{DS} =10V, V _{GS} =4.5V, I _D =1.0A	1.52	nC
ton	V _{DD} =10V, V _{GS} =4.5V, I _D =0.95A, R _G =6Ω	20	ns
^t off	V_{DD} =10V, V_{GS} =4.5V, I _D =0.95A, R _G =6 Ω	25	ns

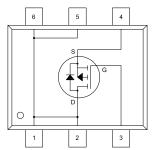
SOT-563 CASE - MECHANICAL OUTLINE





DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
A	0.0027	0.007	0.07	0.18				
В	0.008		0.20					
С	0.017	0.024	0.45	0.60				
D	0.059	0.067	1.50	1.70				
E	0.020		0.50					
F	0.059	0.067	1.50	1.70				
G	0.043	0.051	1.10	1.30				
Н	0.006	0.012	0.15	0.30				
SOT-563 (REV: R2)								

PIN CONFIGURATION



LEAD CODE:

- 1) Drain
- 2) Drain
- 3) Gate
- 4) Source
- 5) Drain 6) Drain

MARKING CODES: CMLDM8120: C81 CMLDM8120G*: C8G

* Device is Halogen Free by design

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SURFACE MOUNT SILICON P-CHANNEL ENHANCEMENT-MODE MOSFET

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